

	Hits	Search Text	DBs
27	43	((substrate or wafer or (silicon near12 \$2oxide) or platen or device or base) same ((form\$4 or deposit\$4 or coat\$3 or film\$3) near22 (resist or photoresist) near26 (via or hole or trench\$3 or (aspect near9 ratio) or opening) near24 (expos\$4 or illuminat\$4 or irradiat\$4)) same ((mask or reticle or photomask) near12 (light\$6shield\$8 or opaque or light\$9block\$5 or opening or transparent or transmit\$6))) and ((photoresist or resist) same (opening or via or hole or trench\$3) same (fill\$4 or remain\$4 or bur\$5 or residu\$3) same ((conformal near16 (deposit\$4 or form\$3)) or bury\$4 or implant\$4)) and ((ILD or inter\$6layer or dielectric or insulat\$4 or thermal\$5oxide) same (layer or film or deposit\$4 or coat\$4)) and ((etch near4 stop) or etch\$4resist\$4)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
28	0	430/313.ccls. and ((substrate or wafer or (silicon near12 \$2oxide) or platen or device or base) same ((form\$4 or deposit\$4 or coat\$3 or film\$3) near22 (resist or photoresist) near26 (via or hole or trench\$3 or (aspect near9 ratio) or opening) near24 (expos\$4 or illuminat\$4 or irradiat\$4)) same ((mask or reticle or photomask) near12 (light\$6shield\$8 or opaque or light\$9block\$5 or opening or transparent or transmit\$6))) and ((photoresist or resist) same (opening or via or hole or trench\$3) same (fill\$4 or remain\$4 or bur\$5 or residu\$3) same ((conformal near16 (deposit\$4 or form\$3)) or bury\$4 or implant\$4)) and ((ILD or inter\$6layer or dielectric or insulat\$4 or thermal\$5oxide) same (layer or film or deposit\$4 or coat\$4)) and ((etch near4 stop) or etch\$4resist\$4)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
29	1	430/311.ccls. and ((substrate or wafer or (silicon near12 \$2oxide) or platen or device or base) same ((form\$4 or deposit\$4 or coat\$3 or film\$3) near22 (resist or photoresist) near26 (via or hole or trench\$3 or (aspect near9 ratio) or opening) near24 (expos\$4 or illuminat\$4 or irradiat\$4)) same ((mask or reticle or photomask) near12 (light\$6shield\$8 or opaque or light\$9block\$5 or opening or transparent or transmit\$6))) and ((photoresist or resist) same (opening or via or hole or trench\$3 or (contact near9 hole) or sublithograph\$7) same (remain\$4 or bur\$5) same develop\$4) and ((ILD or inter\$6layer or dielectric or insulat\$4 or thermal\$5oxide) same (layer or film or deposit\$4 or coat\$4)) and ((etch near4 stop) or etch\$4resist\$4)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
30	1	430/311.ccls. and ((substrate or wafer or (silicon near12 \$2oxide) or platen or device or base) same ((form\$4 or deposit\$4 or coat\$3 or film\$3) near22 (resist or photoresist) near26 (via or hole or trench\$3 or (aspect near9 ratio) or opening) near24 (expos\$4 or illuminat\$4 or irradiat\$4)) same ((mask or reticle or photomask) near12 (light\$6shield\$8 or opaque or light\$9block\$5 or opening or transparent or transmit\$6))) and ((photoresist or resist) same (opening or via or hole or trench\$3) same (fill\$4 or remain\$4 or bur\$5 or residu\$3) same ((conformal near16 (deposit\$4 or form\$3)) or bury\$4 or implant\$4)) and ((ILD or inter\$6layer or dielectric or insulat\$4 or thermal\$5oxide) same (layer or film or deposit\$4 or coat\$4)) and ((etch near4 stop) or etch\$4resist\$4)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
31	4	((substrate or wafer or (silicon near12 \$2oxide) or platen or device or base) same ((form\$4 or deposit\$4 or coat\$3 or film\$3) near22 (resist or photoresist) near26 (via or hole or trench\$3 or (aspect near9 ratio) or opening) near24 (expos\$4 or illuminat\$4 or irradiat\$4)) same ((mask or reticle or photomask) near12 (light\$6shield\$8 or opaque or light\$9block\$5 or opening or transparent or transmit\$6))) and ((photoresist or resist) near16 (opening or via or hole or trench\$3 or (contact near9 hole) or sublithograph\$7) near16 (remain\$4 or bur\$5) near20 develop\$4) and ((ILD or inter\$6layer or dielectric or insulat\$4 or thermal\$5oxide) same (layer or film or deposit\$4 or coat\$4)) and ((etch near4 stop) or etch\$4resist\$4)	US-PGPUB

	Hits	Search Text	DBs
32	10	((substrate or wafer or (silicon near12 \$2oxide) or platen or device or base) same ((form\$4 or deposit\$4 or coat\$3 or film\$3) near22 (resist or photoresist) near26 (via or hole or trench\$3 or (aspect near9 ratio) or opening) near24 (expos\$4 or illuminat\$4 or irradiat\$4)) same ((mask or reticle or photomask) near12 (light\$6shield\$8 or opaque or light\$9block\$5 or opening or transparent or transmit\$6))) and ((photoresist or resist) near16 (opening or via or hole or trench\$3 or (contact near9 hole) or sublithograph\$7) near16 (remain\$4 or bur\$5) near20 develop\$4) and ((ILD or inter\$6layer or dielectric or insulat\$4 or thermal\$5oxide) same (layer or film or deposit\$4 or coat\$4)) and ((etch near4 stop) or etch\$4resist\$4)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
33	1	438/690.ccls. and ((substrate or wafer or (silicon near12 \$2oxide) or platen or device or base) same ((form\$4 or deposit\$4 or coat\$3 or film\$3) near22 (resist or photoresist) near26 (via or hole or trench\$3 or (aspect near9 ratio) or opening) near24 (expos\$4 or illuminat\$4 or irradiat\$4)) same ((mask or reticle or photomask) near12 (light\$6shield\$8 or opaque or light\$9block\$5 or opening or transparent or transmit\$6))) and ((photoresist or resist) same (opening or via or hole or trench\$3) same (fill\$4 or remain\$4 or bur\$5 or residu\$3) same ((conformal near16 (deposit\$4 or form\$3)) or bury\$4 or implant\$4)) and ((ILD or inter\$6layer or dielectric or insulat\$4 or thermal\$5oxide) same (layer or film or deposit\$4 or coat\$4)) and ((etch near4 stop) or etch\$4resist\$4)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB